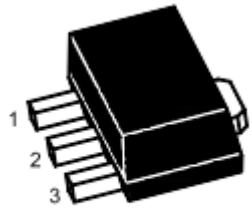
Features

EC762060UB6R

- **PNP Silicon Epitaxial Planar Transistor**
  for high speed switching, DC-DC converter and strobe applications



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Order information

EC762060U XX X

R : Tape reel

B6: SOT89-3L

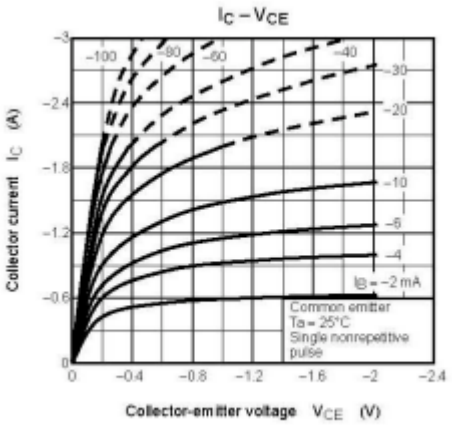
Absolute Maximum Ratings (Ta = 25℃)

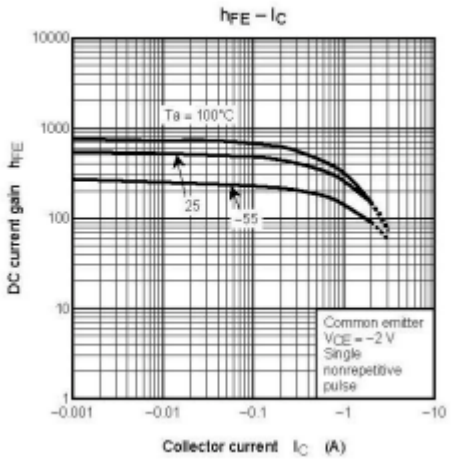
Parameter	Symbol	Value	Unit
Collector Base Voltage	-VCBO	50	V
Collector Emitter Voltage	-VCEO	50	V
Emitter Base Voltage	-VEBO	7	V
Collector Current (DC)	-IC	2	A
Collector Current (Pulse)	-ICP	3.5	A
Base Current	-IB	200	mA
Collector Power Dissipation	Ptot	0.5 1(1)	W
Junction Temperature	Tj	150	℃
Storage Temperature Range	Tstg	- 55 to + 150	℃

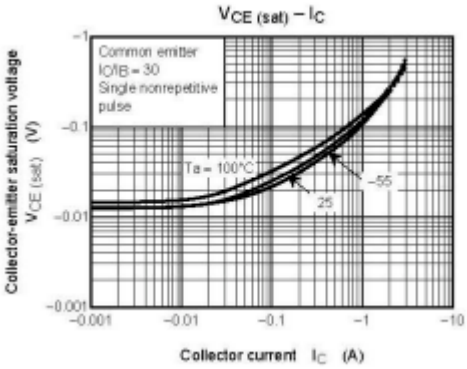
(1) Mounted on a ceramic substrate (250 mm X 0.8 t)

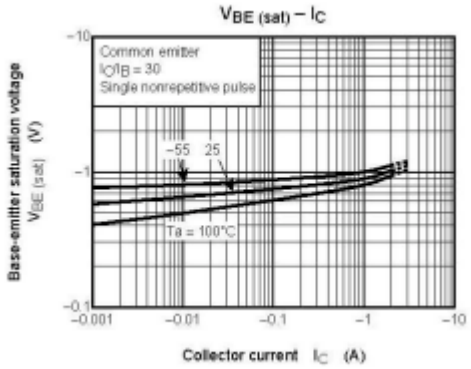
Electrical Characteristics (TA=25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 2 V, $-I_C$ = 300 mA at $-V_{CE}$ = 2 V, $-I_C$ = 1 A	 h_{FE} h_{FE}	 200 100	 - -	 500 -	 - -
Collector Base Cutoff Current at $-V_{CB}$ = 50 V	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 7 V	$-I_{EBO}$	-	-	100	nA
Collector Emitter Breakdown Voltage at $-I_C$ = 10 mA	$-V_{(BR)CEO}$	50	-	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 1 A, $-I_B$ = 33 mA	$-V_{CE(sat)}$	-	-	0.2	V
Base Emitter Saturation Voltage at $-I_C$ = 1 A, $-I_B$ = 33 mA	$-V_{BE(sat)}$	-	-	1.1	V
Collector Output Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz	C_{ob}	-	20	-	pF
Rise Time at $-V_{CC}$ ≈ 30 V, I_{B1} = $-I_{B2}$ = 33 mA, R_L=30 Ω	t_r	-	60	-	ns
Storage Time at $-V_{CC}$ ≈ 30 V, I_{B1} = $-I_{B2}$ = 33 mA, R_L=30 Ω	t_{stg}	-	250	-	ns
Fall Time at $-V_{CC}$ ≈ 30 V, I_{B1} = $-I_{B2}$ = 33 mA, R_L=30 Ω	t_f	-	90	-	ns



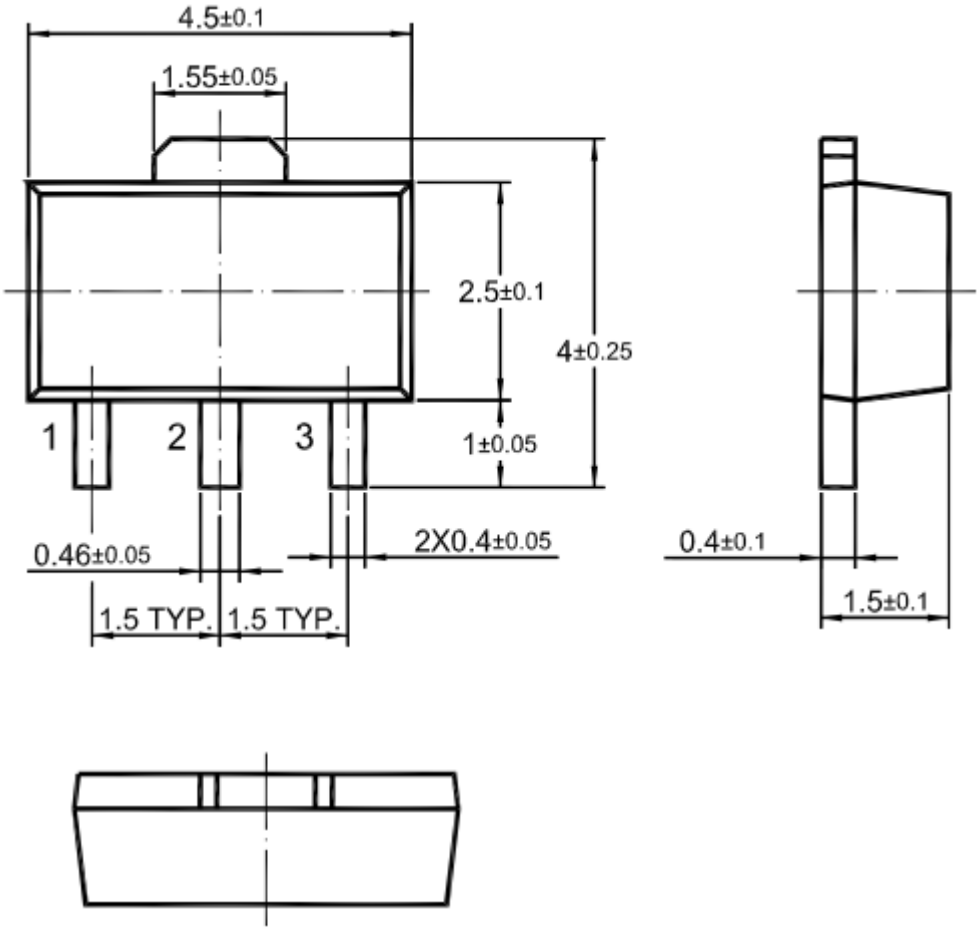






Package Dimensions

SOT-89



Dimensions in mm